
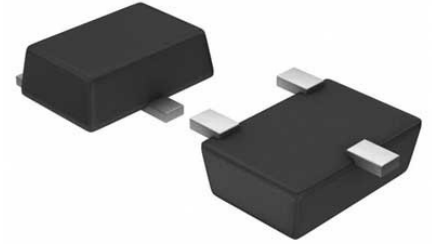


Trans MOSFET P-CH Si 100V 0.12A 3-Pin SOT-23 T/R

Manufacturer:	Microchip Technology, Inc
Package/Case:	SOT-23
Product Type:	Thyristors
RoHS:	RoHS Compliant/Lead free 
Lifecycle:	Active



Images are for reference only

[Inquiry](#)

General Description

VP2110 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown. Vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Key Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low CISS and fast switching speeds
- Excellent thermal stability
- Integral source-to-drain diode
- High input impedance and high gain

Recommended For You

VP3203N3-G

Microchip Technology, Inc
TO-92-3

VP0808L-G

Microchip Technology, Inc
TO-92-3

VP2106N3-G

Microchip Technology, Inc
TO-92

VP0106N3-G

Microchip Technology, Inc
TO-92

2N3823

Microchip Technology, Inc
CAN

2N6661

Microchip Technology, Inc
CAN3

2N4416A

Microchip Technology, Inc
TO-72

APT60GT60BRG

Microchip Technology, Inc
TO-247B

2N4857

Microchip Technology, Inc
CAN

APT45GR65B

Microchip Technology, Inc
TO-247

APT60GT60JRD

Microchip Technology, Inc
MODULE

2N3822

Microchip Technology, Inc
CAN

JANIX2N6284

Microchip Technology, Inc
TO-3

2N6283

Microchip Technology, Inc
TO-3

APT75GN120LG

Microchip Technology, Inc
TO-264L